

Description

The AO3401BI uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

General Features

$V_{DS} = -30V, I_D = -4.2A$

$R_{DS(ON)} < 58m\Omega @ V_{GS} = -10V$

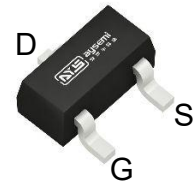
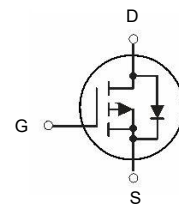
$R_{DS(ON)} < 80m\Omega @ V_{GS} = -4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply


SOT-23


P-Channel MOSFET

Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3401BI	SOT-23	A19T	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	-4.2	A
I_{DM}	Drain Current-Pulsed (Note 1)	-30	A
P_D	Maximum Power Dissipation	1.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	104	°C/W

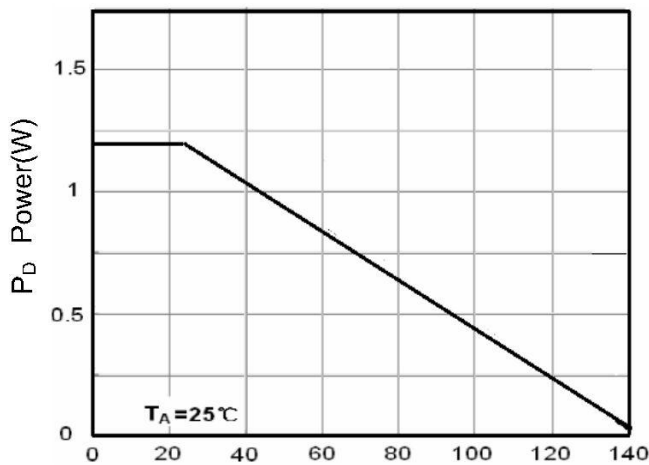
Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.2A	-	48	58	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	60	80	mΩ
		V _{GS} =-2.5V, I _D =-1A	-	85	110	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4.2A	-	10	-	S
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	806	-	PF
Output Capacitance	C _{oss}		-	105	-	PF
Reverse Transfer Capacitance	C _{rss}		-	65	-	PF
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-4.2A V _{GS} =-10V, R _{GEN} =6Ω	-	7	-	nS
Turn-on Rise Time	t _r		-	3	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-4.2A, V _{GS} =-4.5V	-	8.5	-	nC
Gate-Source Charge	Q _{gs}		-	1.8	-	nC
Gate-Drain Charge	Q _{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =-4.2A	-	-	-1.2	V

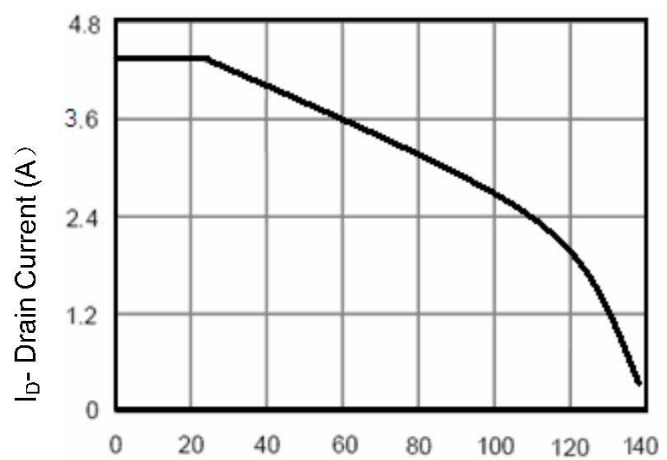
Notes:

- 1、Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2、Surface Mounted on FR4 Board, $t \leq 10$ sec.
- 3、Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 4、Guaranteed by design, not subject to production

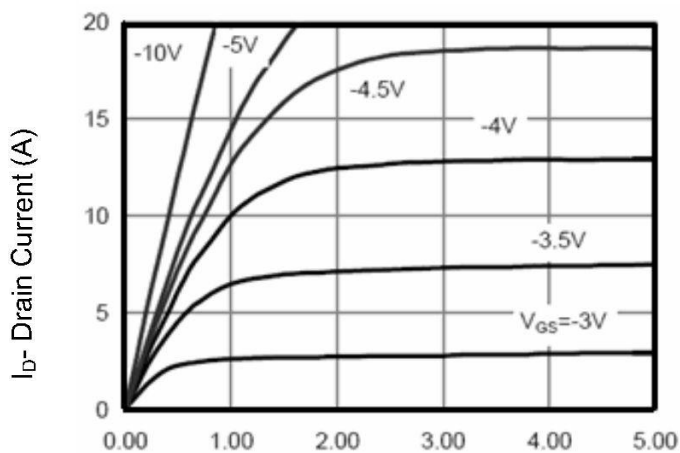
Typical Electrical and Thermal Characteristics



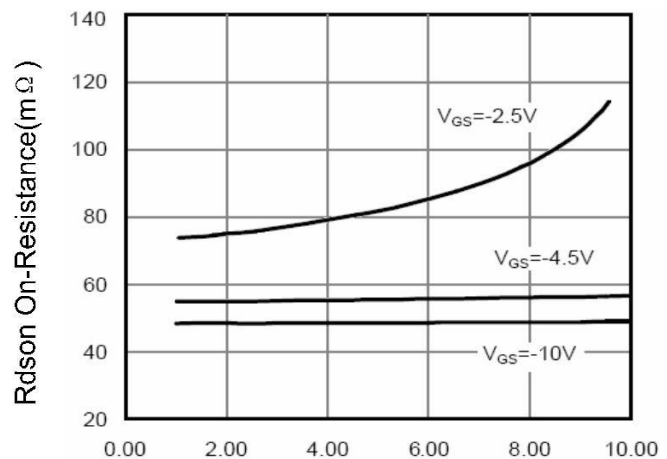
T_J -Junction Temperature($^{\circ}\text{C}$)
Figure 1 Power Dissipation



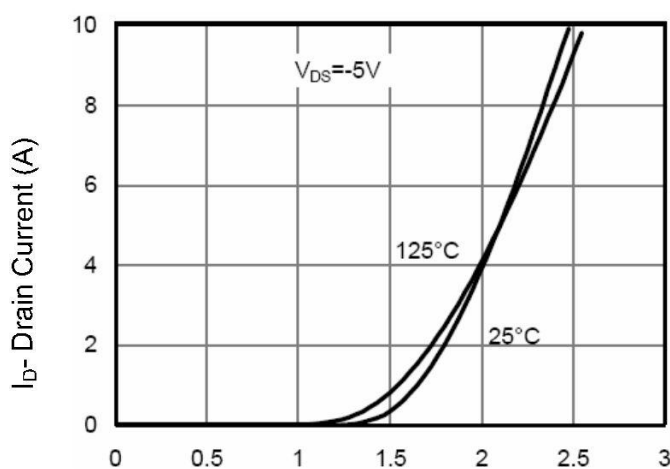
T_J -Junction Temperature($^{\circ}\text{C}$)
Figure 2 Drain Current



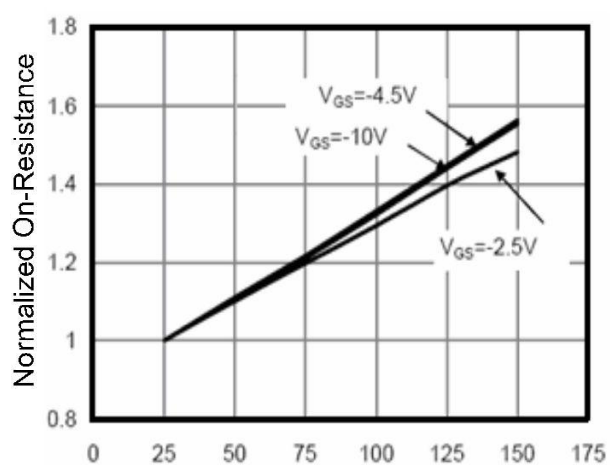
V_{DS} Drain-Source Voltage (V)
Figure 3 Output Characteristics



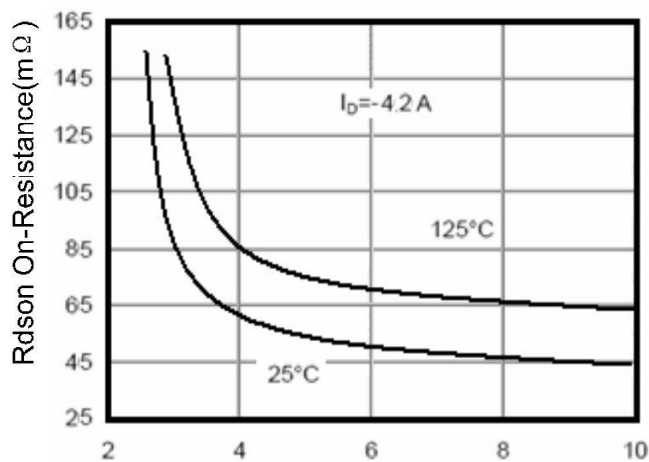
I_D - Drain Current (A)
Figure 4 Drain-Source On-Resistance



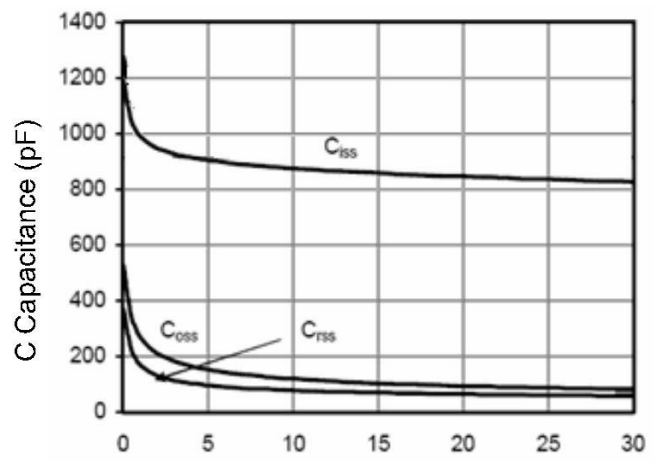
V_{GS} Gate-Source Voltage (V)
Figure 5 Transfer Characteristics



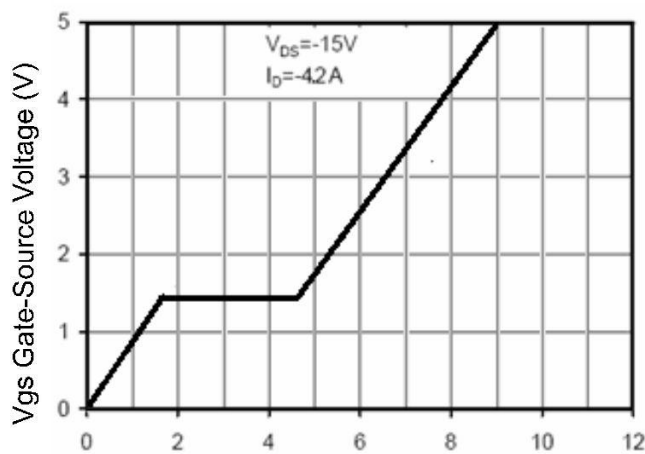
T_J -Junction Temperature($^{\circ}\text{C}$)
Figure 6 Drain-Source On-Resistance



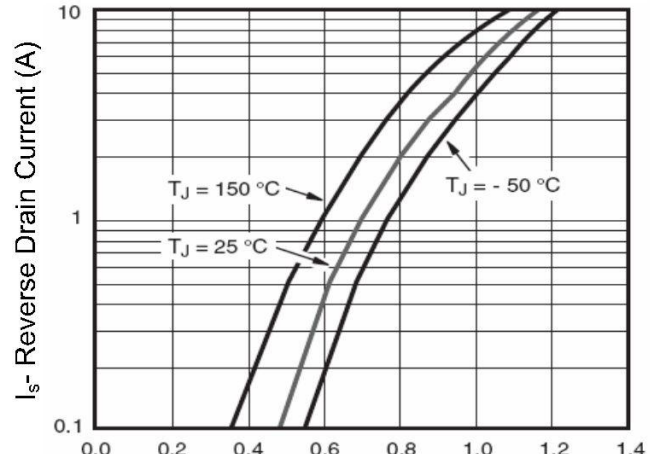
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 8 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 9 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 10 Source- Drain Diode Forward

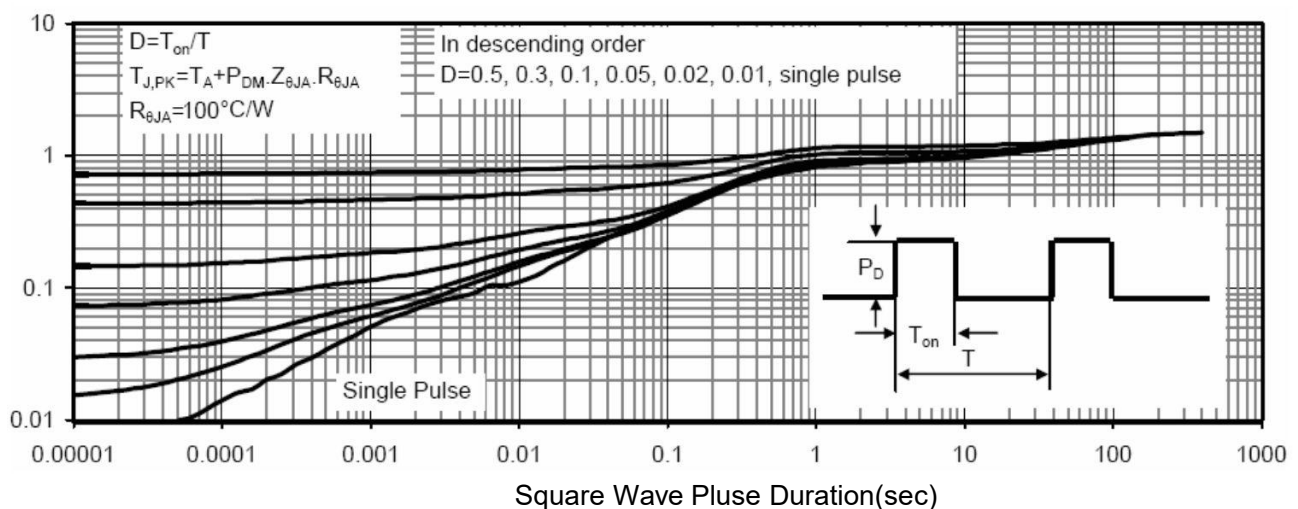
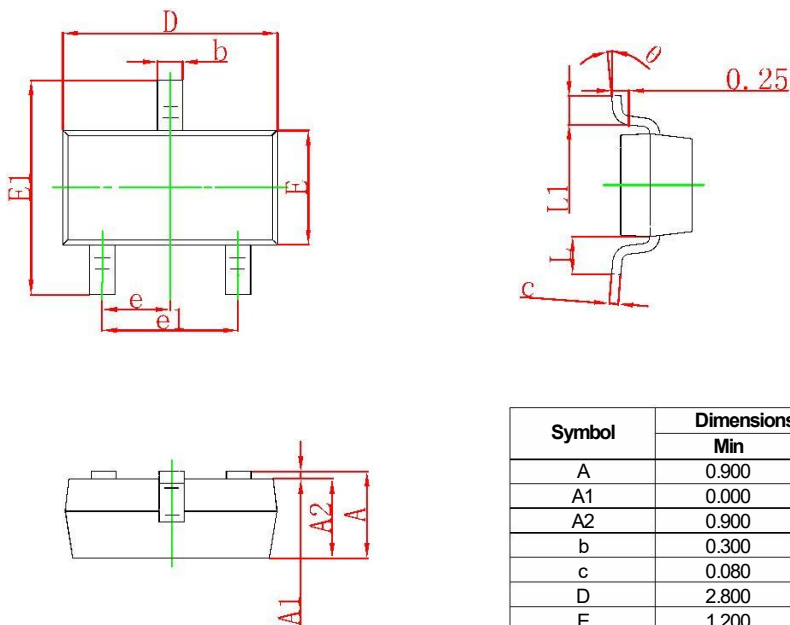


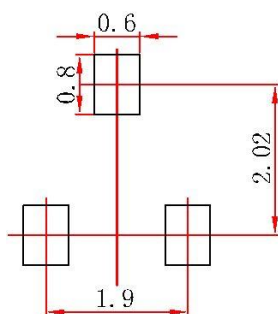
Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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